

FORM PT 01449 (Modified)	ATTY. DOCKET NO. FIS9-2003-0235US1	SERIAL NO. 10/707,841
LIST OF PATENTS AND PUBLICATIONS FOR APPLICANT'S INFORMATION DISCLOSURE STATEMENT	APPLICANT: Haining S. Yang, et al.	
(Use several sheets if necessary)	FILING DATE: 01/16/2004	GROUP: Unassigned 2813

REFERENCE DESIGNATION

U.S. PATENT DOCUMENTS

EXAMINER INITIALS	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE (IF APPRO.)
/JC/	6,228,694 B1	5/8/2001	Doyle et al.			
	6,406,973 B1	6/18/2002	Lee			
	6,281,532 B1	8/28/2001	Doyle et al.			
	5,683,934	11/4/97	Candelaria			
	6,368,931 B1	4/9/2002	Kuhn, et al.			
	5,310,446	5/10/94	Konishi et al.			
	4,853,076	8/1/89	Tsaur et al.			
	US 2002/0090791 A1	7/11/2002	Doyle et al.			
	US 2002/0074598 A1	6/20/2002	Doyle et al.			
	6,509,618 B2	01/21/2003	Jan et al.			
	6,476,462 B2	11/5/2002	Shimizu et al.			
/JC/	6,362,082 B1	3/26/2002	Doyle et al.			
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/JC/	5,565,697	10/15/96	Asakawa et al.			
	US 2003/0040158 A1	2/27/2003	Saitoh			
	US 2002/0086472 A1	7/4/2002	Roberds et al.			
	6,521,964 B1	2/18/2003	Jan et al.			
/JC/	6,506,652	01/14/03	Jan, et al.			

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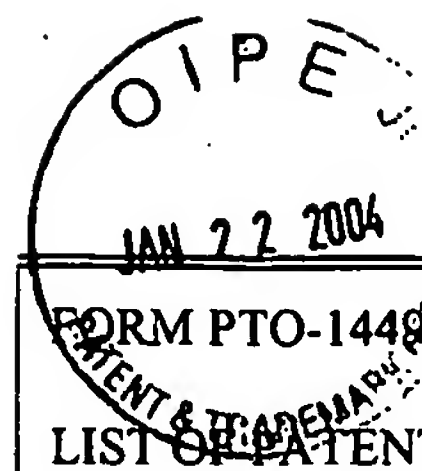
DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
					YES	NO

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EXAMINER /Jack Chen/ (02/04/2008)	DATE CONSIDERED 02/04/2008
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/JC/	5,081,513	1/14/1992	Jackson, et al.			
	3,602,841	8/31/1971	McGroddy			
	6,531,740	3/11/2003	Bosco, et al.			
	6,531,369	3/11/2003	Ozkan, et al.			
	6,501,121	12/31/2002	Yu, et al.			
	6,498,358	12/24/2002	Lach, et al.			
	6,493,497	12/10/2002	Ramdani, et al.			
	6,403,975	6/11/2002	Brunner, et al.			
	6,361,885	3/26/2002	Chou			
	6,255,169	7/3/2001	Li, et al.			
	6,246,095	6/12/2001	Brady, et al.			
	6,165,383	12/26/2000	Chou			
	6,133,071	10/17/2000	Nagai			
	6,046,464	4/4/2000	Schetzina			
/JC/	6,025,280	2/15/2000	Brady, et al.			

FOREIGN PATENT DOCUMENTS

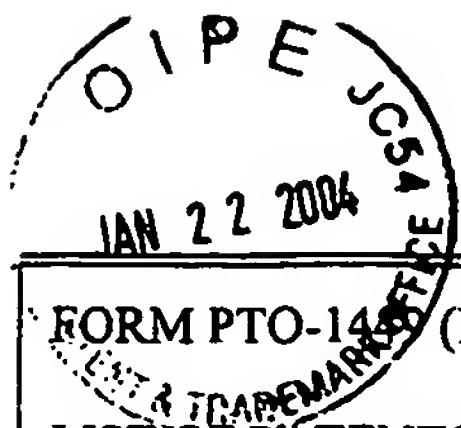
	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
						YES	NO

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EXAMINER INITIALS	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE (IF APPRO.)
/JC/	5,940,736	8/17/1999	Brady, et al.			
	5,880,040	3/9/1999	Sun, et al.			
	5,861,651	1/19/1999	Brasen, et al.			
	5,679,965	10/21/1997	Schetzina			
	5,670,798	9/23/1997	Schetzina			
	5,561,302	10/1/1996	Candelaria			
	5,471,948	12/5/1995	Burroughes, et al.			
	5,459,346	10/17/1995	Asakawa, et al.			
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	5,371,399	12/6/1994	Burroughes, et al.			
	5,108,843	4/28/1992	Ohtaka, et al.			
	5,060,030	10/22/1991	Hoke			
	4,958,213	9/18/1990	Eklund, et al.			
/JC/	4,665,415	5/12/1987	Esaki, et al.			

FOREIGN PATENT DOCUMENTS

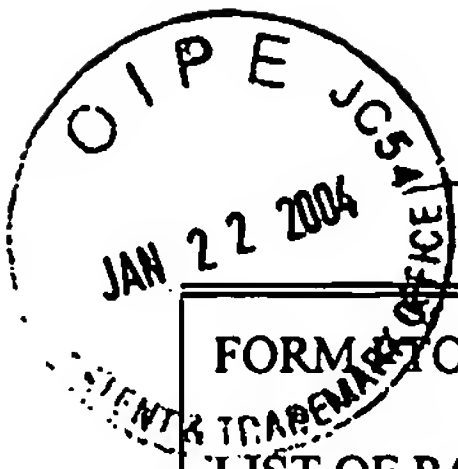
	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
						YES	NO

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REFERENCE DESIGNATION	U.S. PATENT DOCUMENTS
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EXAMINER INITIALS	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE (IF APPRO.)
/JC/	5,989,978	11/23/1999	Peidous			
	6,284,626	9/4/2001	Kim			
	6,274,444	8/14/2001	Wang			
	6,261,964	7/17/2001	Wu, et al.			
	6,221,735	4/24/2001	Manley, et al.			
	6,117,722	9/12/2000	Wuu, et al.			
	6,107,143	8/22/2000	Park, et al.			
	6,090,684	7/18/2000	Ishitsuka, et al.			
	6,066,545	5/23/2000	Doshi, et al.			
	6,008,126	12/28/1999	Leedy			
	5,946,559	8/31/1999	Leedy			
	5,840,593	11/24/1998	Leedy			
	5,592,018	1/7/1997	Leedy			
	5,592,007	1/7/1997	Leedy			
/JC/	5,571,741	11/5/1996	Leedy			

FOREIGN PATENT DOCUMENTS

DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
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ATTY. DOCKET NO.
FIS9-2003-0235US1SERIAL NO.
10/707,841LIST OF PATENTS AND PUBLICATIONS FOR
APPLICANT'S INFORMATION DISCLOSURE
STATEMENTAPPLICANT:
Haining S. Yang, et al.

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FILING DATE:
01/16/2004GROUP:
Unassigned 2813

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U.S. PATENT DOCUMENTS

EXAMINER INITIALS	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE (IF APPRO.)
/JC/	5,557,122	9/17/1996	Shrivastava, et al.			
	5,354,695	10/11/1994	Leedy			
	5,134,085	7/28/1992	Gilgen, et al.			
	5,006,913	4/9/1991	Sugahara, et al.			
	4,952,524	8/28/1990	Lee, et al.			
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	2002/0086497	07-04-2002	Kwok			
	5,960,297	09-28-1999	Saki			
	6,403,486	06-11-2002	Lou			
	6,284,623	09-04-2001	Zhang et al.			
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	2003/0057184	03-27-2003	Yu et al.			
	6,265,317	07-24-2001	Chiu et al.			
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	6,461,936	10-08-2002	von Ehrenwall			
	6,319,794	11-20-2001	Akatsu et al.			
/JC/	2001/0009784	07-26-2001	Ma et al.			

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DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
					YES	NO

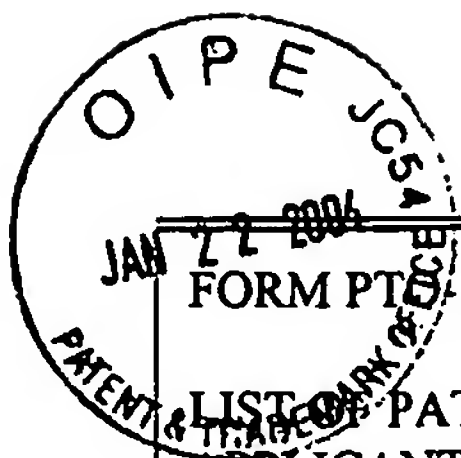
OTHER ART (Including Author, Title, Date, Pertinent Pages, etc.)

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DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION
					YES NO

OTHER ART (Including Author, Title, Date, Pertinent Pages, etc.)

/JC/		Kern Rim, et al., "Transconductance Enhancement in Deep Submicron Strained-Si <i>n</i> -MOSFETs", International Electron Devices Meeting, 26, 8, 1, IEEE, September 1998.
		Kern Rim, et al., "Characteristics and Device Design of Sub-100 nm Strained Si N- and PMOSFETs", 2002 Symposium On VLSI Technology Digest of Technical Papers, IEEE, pp 98-99.
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		A. Shimizu, et al., "Local Mechanical-Stress Control (LMC): A New Technique for CMOS-Performance Enhancement", International Electron Devices Meeting, IEEE, March 2001.
/JC/		K. Ota, et al., "Novel Locally Strained Channel Technique for high Performance 55nm CMOS", International Electron Devices Meeting, 2.2.1, IEEE, February 2002.

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FORM PTO-1449

U.S. Department of Commerce
Patent and Trademark OfficeAtty. Docket No.
P27160Application No.
10/707,841INFORMATION DISCLOSURE STATEMENT
BY APPLICANT
(Use several sheets if necessary)Applicant
Haining S. YANGFiling Date
January 16, 2004Group
2813

U.S. PATENT DOCUMENTS

EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
/JC/		US 2002/0063292 A1	5-30-2002	Armstrong et al.			
		US 2003/0032261 A1	2-13-2003	Yeh et al.			
		US 2003/0040158 A1	2-27-2003	Saitoh			
		US 2004/0238914 A1	12-2-2004	Deshpande et al.			
		US 2004/0262784 A1	12-30-2004	Doris et al.			
		US 2005/0040460 A1	2-24-2005	Chidambarao et al.			
		US 2005/0082634 A1	4-21-2005	Doris et al.			
		US 2005/0093030 A1	5-5-2005	Doris et al.			
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		US 2005/0106799 A1	5-19-2005	Doris et al.			
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		US 2005/0194699 A1	9-8-2005	Belyansky et al.			
		US 2005/0236668 A1	10-27-2005	Zhu et al.			
		US 2005/0245017 A1	11-3-2005	Belyansky et al.			
		US 2005/0280051 A1	12-22-2005	Chidambarao et al.			
		US 2005/0282325 A1	12-22-2005	Belyansky et al.			
		US 2006/0027868 A1	2-9-2006	Doris et al.			
		US 2006/0057787 A1	3-16-2006	Doris et al.			
		US 2006/0060925 A1	3-23-2006	Doris et al.			
		6,483,171	11-19-2002	Forbes et al.			
		6,831,292	12-14-2004	Currie et al.			
		6,717,216	4-6-2004	Doris et al.			
		6,825,529	11-30-2004	Chidambarao et al.			
		7,015,082	3-21-2006	Doris et al.			
		6,974,981	12-13-2005	Chidambarao et al.			
/JC/		6,977,194	12-20-2005	Belyansky et al.			

FOREIGN PATENT DOCUMENTS

		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION YES NO
/JC/		JP 64-76755	3-22-1989	Japan			X

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

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FORM PTO-1449		U.S. Department of Commerce Patent and Trademark Office		Atty. Docket No. P27160		Application No. 10/707,841	
INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Use several sheets if necessary)				Applicant Haining S. YANG			
				Filing Date January 16, 2004		Group 2813	
U.S. PATENT DOCUMENTS							
EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
FOREIGN PATENT DOCUMENTS							
		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION YES NO
OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)							
/JC/		G. Zhang, et al., "A New 'Mixed-Mode' Reliability Degradation Mechanism in Advanced Si and SiGe Bipolar Transistors." IEEE Transactions on Electron Devices, vol. 49, no. 12, December 2002, pp. 2151-56.					
		H.S. Momose, et al., "Temperature Dependence of Emitter-Base Reverse Stress Degradation and its Mechanism Analyzed by MOS Structures." 1989 IEEE, Paper 6.2, pp. 140-143.					
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		S.R. Sheng, et al., "Degradation and Recovery of SiGe HBTs Following Radiation and Hot-Carrier Stressing." pp. 14-15.					
		Z. Yang, et al., "Avalanche Current Induced Hot Carrier Degradation in 200 GHz SiGe Heterojunction Bipolar Transistors." pp. 1-5.					
		H. Li, et al., "Design of W-Band VCOs with High Output Power for Potential Application in 77 GHz Automotive Radar Systems." 2003, IEEE GaAs Digest, pp. 263-66.					
		H. Wurzer, et al., "Annealing of Degraded non-Transistors-Mechanisms and Modeling." IEEE Transactions on Electron Devices, vol. 41, no. 4, April 1994, pp. 533-38.					
		B. Doyle, et al., "Recovery of Hot-Carrier Damage in Reoxidized Nitrided Oxide MOSFETs." IEEE Electron Device Letters, vol. 13, no. 1, January 1992, pp. 38-40					
		H.S. Momose, et al. "Analysis of the Temperature Dependence of Hot-Carrier-Induced Degradation in Bipolar Transistors for Bi-CMOS." IEEE Transactions on Electron Devices, vol. 41, no. 6, June 1994, pp. 978-987.					
		M. Khater, et al., "SiGe HBT Technology with $F_{max}/F_t = 350/300$ GHz and Gate Delay Below 3.3 ps". 2004 IEEE, 4 pages.					
		J.C. Bean, et al., "GEx Si 1-x/Si Strained-Layer Superlattice Grown by Molecular Beam Epitaxy". J. Vac. Sci. Technol. A 2(2), Apr.-June 1984, pp. 436-440.					
		J.H. Van Der Merwe, "Regular Articles". Journal of Applied Physics, Volume 34, No. 1, January 1963, pp. 117-122.					
		J.W. Matthews, et al., "Defects in Epitaxial Multilayers". Journal of Crystal Growth 27 (1974), pp. 118-125.					
		Subramanian S. Iyer, et al. " Heterojunction Bipolar Transistors Using Si-Ge Alloys". IEEE Transactions on Electron Devices, Vol. 36, No. 10, October 1989, pp. 2043-2064					
		R.H.M. Van De Leur, et al., "Critical Thickness for Pseudomorphic Growth of Si/Ge Alloys and Superlattices". J. Appl. Phys. 64 (6), 15 September 1988, pp. 3043-3050					
		D.C. Houghton, et al., "Equilibrium Critical Thickness for Si 1-x GEx Strained Layers on (100) Si". Appl. Phys. Lett. 56 (5), 29 January 1990, pp. 460-462					
/JC/		Q. Quyang et al., "Two-Dimensional Bandgap Engineering in a Novel Si/SiGe pMOSFET with Enhanced Device Performance and Scalability". 2000, IEEE, pp. 151-154.					
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